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(54) **SEMICONDUCTOR DEVICE AND METHOD
FOR FABRICATING THE SAME**

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ABSTRACT

A semiconductor device includes: a substrate; a plurality of memory cells positioned over the substrate, each of the plurality of memory cells having a multi-layer structure including a memory pattern; a sealing layer pattern filling a lower portion of a space between the memory cells, the lower portion being positioned below a bottom surface of the memory pattern; a liner layer pattern formed along a surface of an upper portion of the space to partially fill the upper portion; and a dielectric layer pattern filling a remaining portion of the space unfilled by the sealing layer pattern and the liner layer pattern.

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